NSN 5961-01-337-2045

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-337-2045 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.180 inches **Terminal Length:** Between 1.000 inches and 1.500 inches **Overall Diameter:** Between 0.056 inches and 0.075 inches **Function For Which Designed:** Switching **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, dc and 75.0 working peak reverse voltage **Current Rating Per Characteristic:** 20.00 milliamperes forward current, average absolute and 1.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Nuclear hardness critical items; junction pattern arrangement: pn **Nuclear Hardness Critical Feature:** Hardened **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0